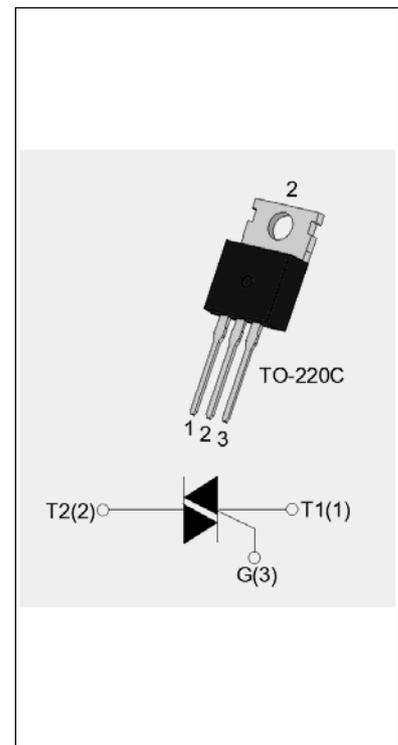




The T3035H-8C triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. Compared to traditional triacs, T3035H-8C provides a very high switching capability up to junction temperatures of 150°C. From T2 terminals to external heatsink. Package TO-220C is RoHS compliant.



Symbol	Value	Unit
$I_{T(RMS)}$	30	A
V_{DRM}/V_{RRM}	800	V
$I_{GT} / /$	35/35/35	mA

Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-150	
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	800	V
RMS on-state current ($T_c = 119^\circ\text{C}$)	$I_{T(RMS)}$	30	A
Non repetitive surge peak on-state current (full cycle, $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	270	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		297	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	365	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=150^\circ\text{C}$)	di/dt	100	$\text{A}/\mu\text{s}$
Peak gate current ($t_p=20\mu\text{s}$, $T_j=150^\circ\text{C}$)	I_{GM}	4	A
Average gate power dissipation ($T_j=150^\circ\text{C}$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W

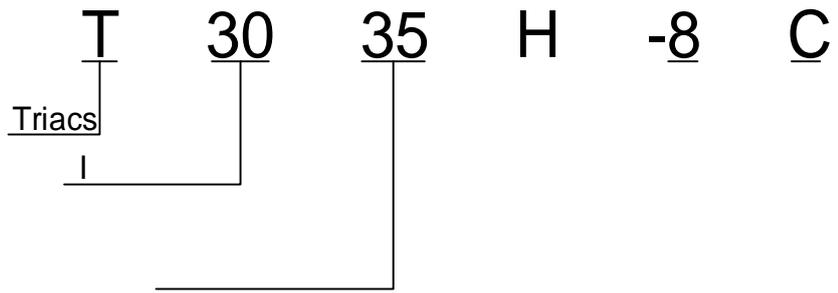


Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	1	kV
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($T_j=25$ unless otherwise specified)

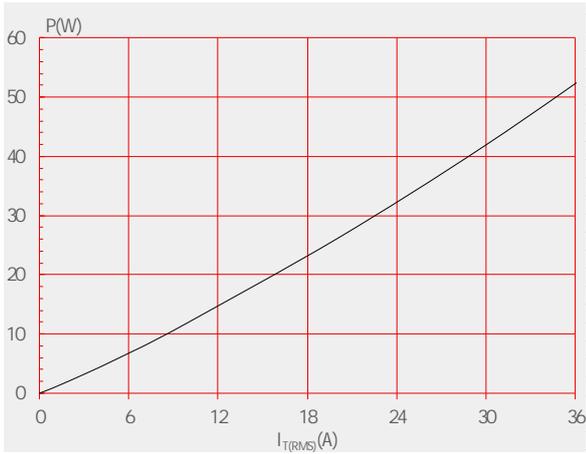
I_{GT}	$V_D=12V$ $R_L=33$	- -	MAX.	35	mA
V_{GT}		- -	MAX.	1.3	V
V_{GD}	$V_D=V_{DRM}$ $T_j=150$ $R_L=3.3K$	- -	MIN.	0.15	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	70	mA
				80	
I_H	$I_T=500mA$		MAX.	50	mA
dV/dt	$V_D=540V$ Gate Open $T_j=150$		MIN.	1000	V/ μs
$(dI/dt)_c$	$(dV/dt)_c=20V/\mu s$, $T_j=150$		MIN.	18	A/ms
t_{on}	$I_G=40mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25$		TYP.	10	μs
t_{off}				80	

V_{TM}	$I_{TM}=42A$ $t_p=380\mu s$	$T_j=25$	1.5	V
V_{TO}	Threshold voltage	$T_j=150$	0.7	V
R_D	Dynamic resistance	$T_j=150$	16	m
I_{DRM}	R $V_D=V_{DRM}$ $V_R=V_{RRM}$	TPara	5	D

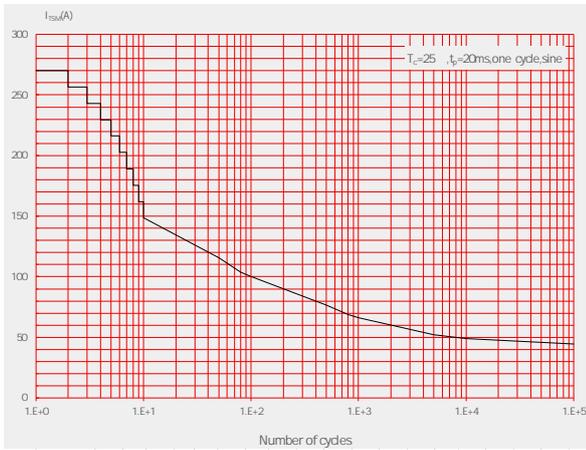




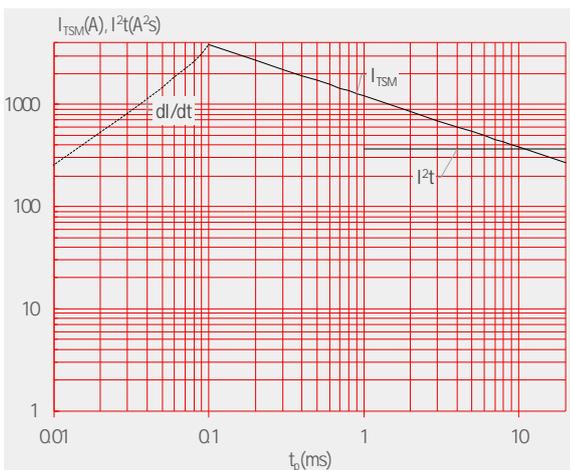
Maximum power dissipation versus RMS on-state current



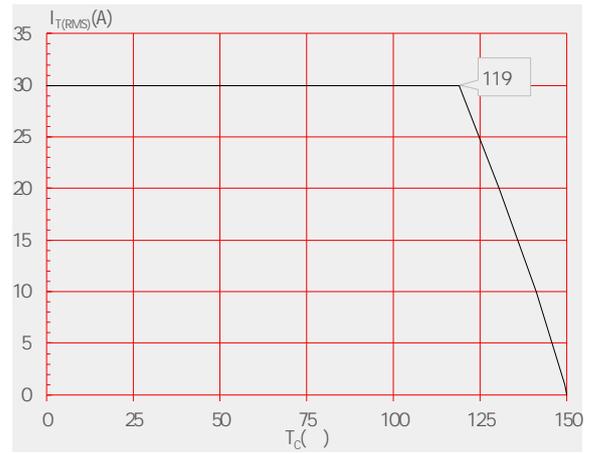
Surge peak on-state current versus number of cycles



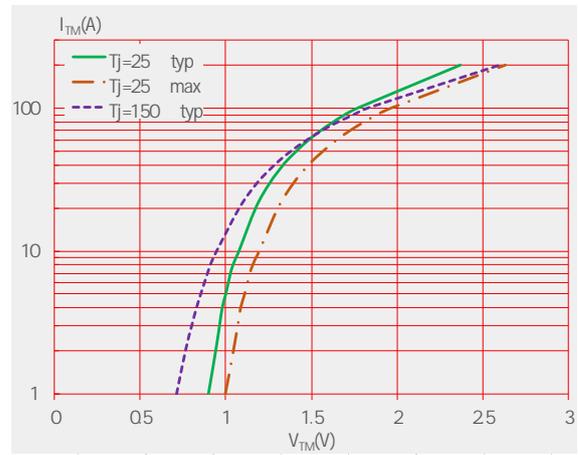
Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($di/dt < 100\text{A}/\mu\text{s}$)



RMS on-state current versus case temperature



On-state characteristics



Relative variations of gate trigger current, holding current and latching current versus junction temperature

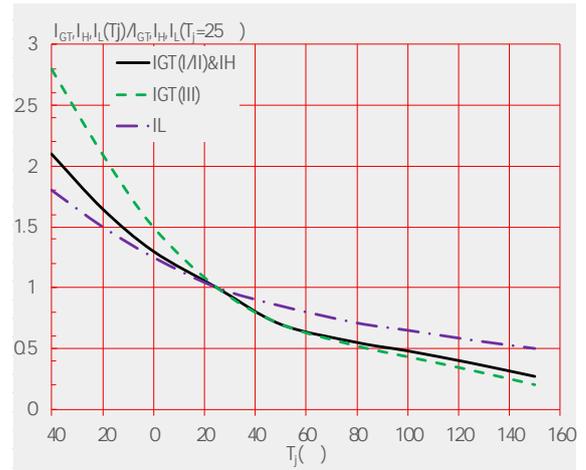
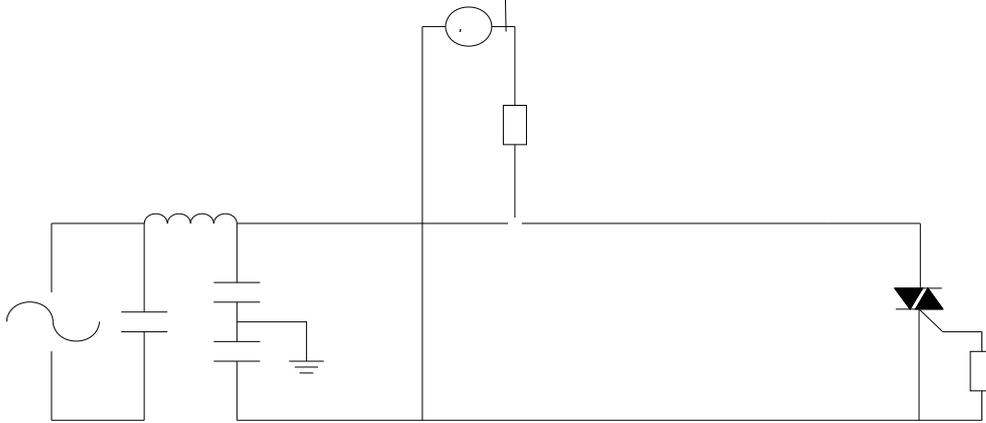


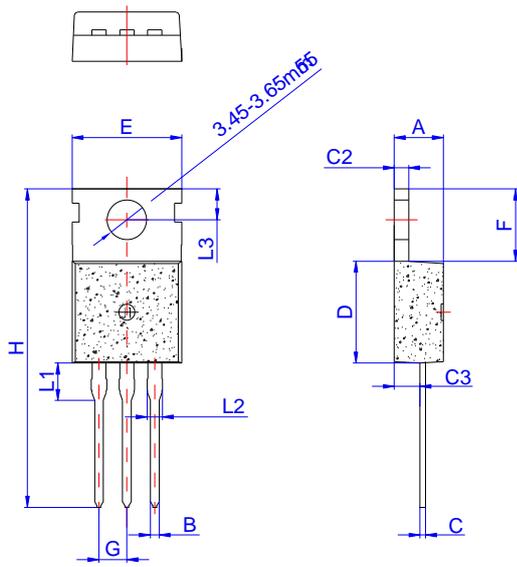


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards





Date	Revision	Changes
Apr. , 2023	A.1.0	Last updated



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.25		1.35	0.049		0.053
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.390		0.406
F	6.30		6.90	0.248		0.272
G	2.40			0.094		
H	28.0		29.8	1.102		1.173
L1	2.70					0.130
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116



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